

MONOLITHIC 1-WATT POWER AMPLIFIER



. . . designed to amplify signals to 300 kHz with one watt delivered to a direct or capacitively coupled load.

- Low Total Harmonic Distortion 0.4% typical at 1 Watt
- Low Output Impedance 0.2 ohm
- Excellent Gain Temperature Stability

MAXIMUM RATINGS ($T_C = 25^{\circ}C$ unless otherwise noted)

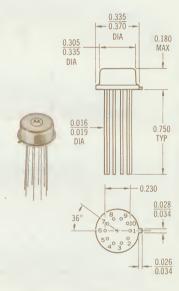
Rating	Symbol	Value	Unit
Total Power Supply Voltage	_V ⁺ ₊ _V ⁻	18	Vdc
Peak Load Current	Iout	0.5	Amp
Audio Output Power	Pout	1.8	Watt
Power Dissipation (package limitation) TA = 25°C	P _D	600	mW
Derate above 25°C		4.8	mW/°C
$T_C = 25^{\circ}C$		1.8	Watts
Derate above 25°C		14.4	mW/°C
Operating Temperature Range	T _C	-55 to +125	°C
Storage Temperature Range	Tstg	-55 to +150	°C

MC1554G

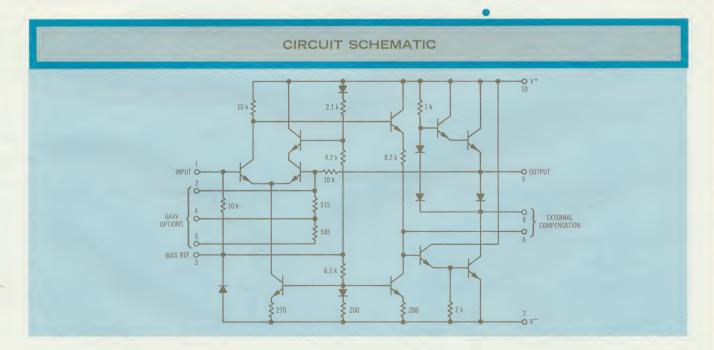
1-WATT
POWER AMPLIFIER
INTEGRATED CIRCUIT

MONOLITHIC SILICON EPITAXIAL PASSIVATED

MARCH 1967 - DS 9069



Pin 7 Electrically Connected to Can



MOTOROLA Semiconductor Products Inc.



MC1554G

Characteristic Definitions	Characteristic	R _L (ohms)	Gain Option*	Symbol	Min	Тур	Max	Unit
	Output Power	16	-	Pout	1.0	1.1	-	Watt
+16 V	Power Dissipation (@Pout = 1.0 W)	16	-	$^{\mathrm{P}}\mathrm{_{D}}$	-	0.9	1.2	Watt
\$ 10	Voltage Gain	16	10	A _V	8.0	10	12	V/V
		16	18		-	18	-	
e _{in} Z _{out} R _L e _{out}		16	36		-	36	-	
÷ , ÷	Input Impedance	-	10	z _{in}	7.0	10	-	kΩ
	Output Impedance	-	10	Zout		0.2	-	Ω
+16 V	Power Bandwidth	16	10		_	270	_	kHz
$V_{\text{out}}(\text{dc}) = \frac{V+}{2}$	(for e _{out} < 5% THD)	16	18		_	250	_	
3011		16	36			210	-	
Pin (1)	Total Harmonic Distortion (for $e_{\rm in} < 0.05\%$ THD, f = 20 Hz to 20 kHz)			THD				%
	P _{out} = 1.0 Watt (sinewave)	16	10		-	0.4	-	
e_{out} = 0.1 Watt (sinewave)	16	10		-	0.5	-		
+16 V	Zero Signal Current Drain	∞	-	ID	-	11	15	mAdc
open O	Output Noise Voltage	16	10	v _N	-	0.3	-	mV RMS
9 V _{our} (dc)	Output Quiescent Voltage (Split Supply Operation)	16	-	V _{out} (dc)	-	±10	±30	mVdc
V+	Positive Supply Sensitivity (V constant)	99	-	S ⁺	-	-40	-	mV/V
open δ V_{out} V_{out} V_{out} V_{out} V_{out} V_{out} V_{out}	Negative Supply Sensitivity (V ⁺ constant)	∞0	-	s ⁻	-	-40	-	mV/V

 $\ensuremath{^{*}}$ To obtain the voltage gain characteristic desired, use the following pin connections:

Voltage Gain

Pin Connection

10 18 36

Pins 2 and 4 open, Pin 5 to ac ground Pins 2 and 5 open, Pin 4 to ac ground Pin 2 connected to Pin 5, Pin 4 to ac ground

TYPICAL CONNECTIONS

FIGURE 2 — SPLIT SUPPLY OPERATION VOLTAGE GAIN (A_V) = 10, $f_{\text{LOW}} \approx 25 \text{ Hz}$

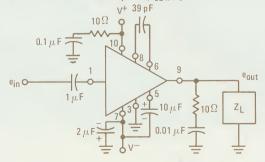
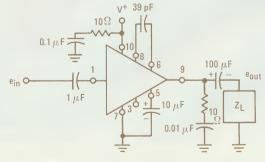


FIGURE 3 — SINGLE SUPPLY OPERATION VOLTAGE GAIN (A_V)= 10, $\rm f_{LOW} \approx 100~Hz$



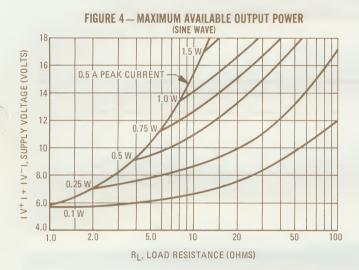
RECOMMENDED OPERATING CONDITIONS

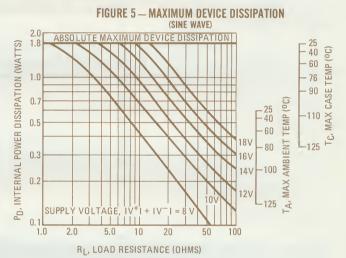
In order to avoid local VHF instability, the following set of rules must be adhered to:

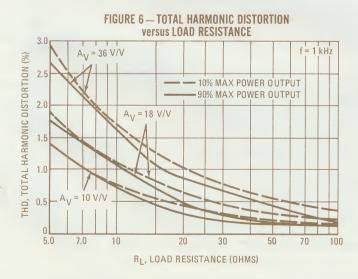
- 1. An R-C stabilizing network (0.1 μ F in series with 10 ohms) should be placed directly from pin 9 to ground, as shown in Figures 2 and 3, using short leads, to eliminate local VHF instability caused by lead inductance to the load.
- 2. Excessive lead inductance from the V+ supply to pin 10 can cause high frequency instability. To prevent this, the V+ by-pass capacitor should be connected with short leads from the V+ pin to ground. If this capacitor is remotely located a series R-C network (0.1 μF and 10 ohms) should be used directly from pin 10 to ground as shown in Figures 2 and 3.
- Lead lengths from the external components to pins 7, 9, and 10 of the package should be as short as possible to insure good VHF grounding for these points.

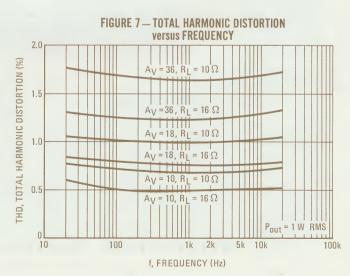
Due to the large bandwidth of the amplifier, coupling must be avoided between the output and input leads. This can be assured by either (a) use of short leads which are well isolated, (b) narrow-banding the overall amplifier by placing a capacitor from pin 1 to ground to form a low-pass filter in combination with the source impedance, or (c) use of a shielded input cable. In applications which require upper band-edge control the input low-pass filter is recommended.

TYPICAL CHARACTERISTICS

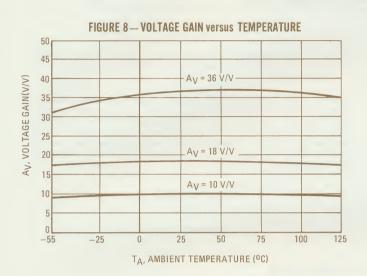


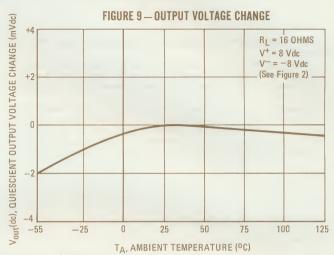


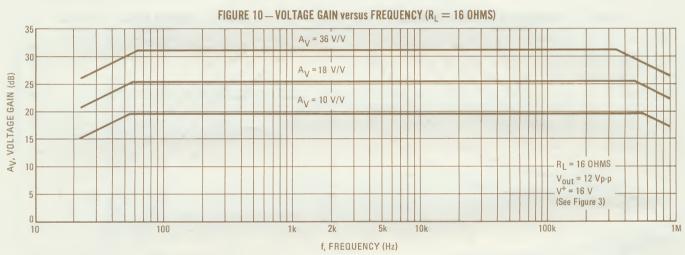


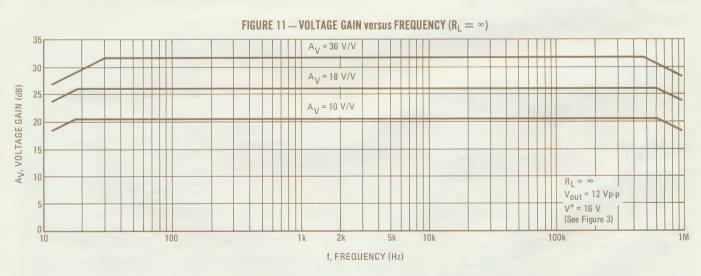


TYPICAL CHARACTERISTICS











MOTOROLA Semiconductor Products Inc.

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